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H11C1X, H11C2X, H11C3X, H11C4X, H11C5X, H11C6X
H11C1, H11C2, H11C3, H11C4, H11C5, H11C6

PHOTON COUPLED ISOLATOR Ga As INFRARED EMITTING DIODE & LIGHT ACTIVATED SCR

Jameco Part Number 18833

APPROVALS

- UL recognised, File No. E91231

'X' SPECIFICATION APPROVALS

- VDE 0884 in 2 available lead forms : -
  - STD
  - G form

DESCRIPTION

The H11C_ series are optically coupled isolators consisting of infrared light emitting diode and a light activated silicon controlled rectifier in a standard 6pin dual in line plastic package.

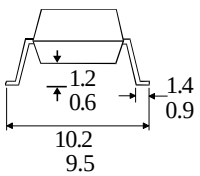
FEATURES

- Options :-
  10mm lead spread - add G after part no.
  Surface mount - add SM after part no.
  Tape&reel - add SMT&R after part no.
- High Isolation Voltage ($5.3kV_{RMS}$, $7.5kV_{PK}$)
- High Surge Anode Current (5.0 A)
- High Blocking Voltage (200V*[1], 400V*[1])
- Low Turn on Current (5mA typical)
- All electrical parameters 100% tested
- Custom electrical selections available

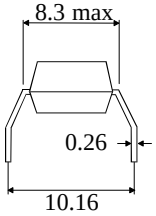
APPLICATIONS

- 10A, T²L compatible, Solid State Relay
- 25W Logic Indicator Lamp Driver
- 400V Symmetrical transistor coupler

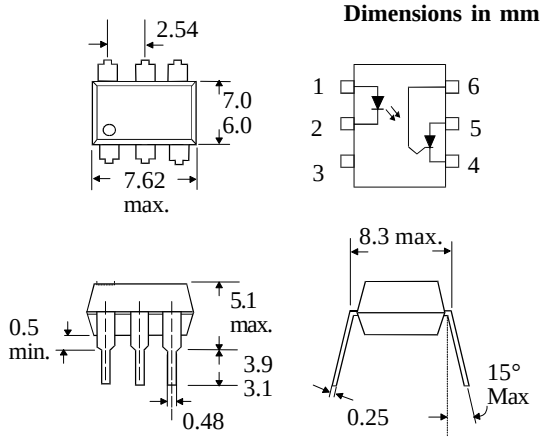
OPTION SM
SURFACE MOUNT



OPTION G



Dimensions in mm



ABSOLUTE MAXIMUM RATINGS
(25°C unless otherwise specified)

Storage Temperature	-55°C to + 150°C
Operating Temperature	-55°C to + 100°C
Lead Soldering Temperature (1/16 inch (1.6mm) from case for 10 secs)	260°C

INPUT DIODE

Forward Current	60mA
Forward Current (Peak) (1µs pulse, 300 pps)	3A
Reverse Voltage	6V
Power Dissipation	100mW

DETECTOR

Peak Forward Voltage	
H11C1, H11C2, H11C3	200V*[1]
H11C4, H11C5, H11C6	400V*[1]
Peak Reverse Gate Voltage	6V
RMS On-state Current	300mA
Peak On-state Current (100µs, 1% duty cycle)	10A
Surge Current (10ms)	5A
Power Dissipation	300mW

*1 IMPORTANT : A resistor must be connected between gate and cathode (pins 4 & 6) to prevent false firing (R_{GK} < 56kΩ)

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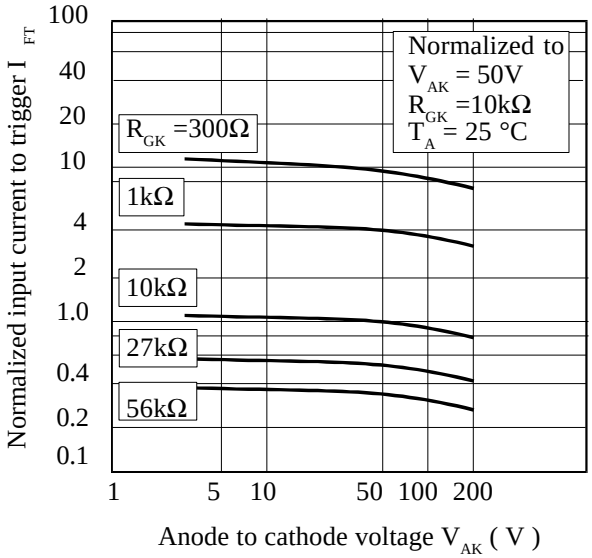
ELECTRICAL CHARACTERISTICS (T_A= 25°C Unless otherwise noted)

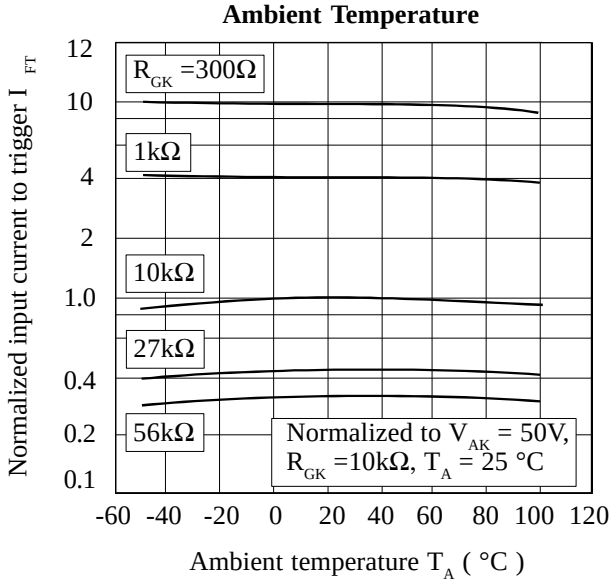
PARAMETER		MIN	TYP	MAX	UNITS	TEST CONDITION
Input	Forward Voltage (V_F)		1.2	1.5	V	I_F = 10mA
	Reverse Voltage (V_R)	3			V	I_R = 10µA
Output (note 2)	Peak Off-state Voltage (V_{DM})					
	H11C1, H11C2, H11C3	200			V	R_{GK}=10kΩ, I_D= 50µA, T_A= 100°C
	H11C4, H11C5, H11C6	400			V	R_{GK}=10kΩ,I_D=150µA, T_A=100°C
	Peak Reverse Voltage (V_{RM})					
	H11C1, H11C2, H11C3	200			V	R_{GK}=10kΩ, I_D= 50µA, T_A=100°C
	H11C4, H11C5, H11C6	400			V	R_{GK}=10kΩ,I_D=150µA, T_A=100°C
	On-state Voltage (V_{TM})		1.1	1.3	V	I_{TM} = 300mA
	Off-state Current (I_{DM})					
	H11C1, H11C2, H11C3			50	µA	R_{GK}=10kΩ, I_F= 0, V_{DM}=200V, T_A=100°C
	H11C4, H11C5, H11C6			150	µA	R_{GK}=10kΩ, I_F= 0, V_{DM}=400V, T_A=100°C
	Reverse Current (I_R)					
	H11C1, H11C2, H11C3			50	µA	R_{GK}=10kΩ, I_F= 0, V_{DM}=200V, T_A=100°C
	H11C4, H11C5, H11C6			150	µA	R_{GK}=10kΩ, I_F= 0, V_{DM}=400V, T_A=100°C
Coupled	Input Current to Trigger (I_{FT}) (note 2)					
	H11C1, H11C2, H11C4, H11C5			20	mA	V_{AK} =50V, R_{GK}=10kΩ
	H11C3, H11C6			30	mA	V_{AK} =50V, R_{GK}=10kΩ
	H11C1, H11C2, H11C4, H11C5			11	mA	V_{AK}=100V, R_{GK}=27kΩ
	H11C3, H11C6			14	mA	V_{AK}=100V, R_{GK}=27kΩ
	Coupled dv/dt, Input to Output (dv/dt)	500			V/µs	
	Input to Output Isolation Voltage V_{ISO}	5300			V_{RMS}	See note 1
		7500			V_{PK}	See note 1
	Input-output Isolation Resistance R_{ISO}	10^{11}			Ω	V_{IO} = 500V (note 1)
	Input-output Capacitance Cf			2	pF	V = 0, f =1MHz

Note 1 Measured with input leads shorted together and output leads shorted together.
Note 2 Special Selections are available on request. Please consult the factory.

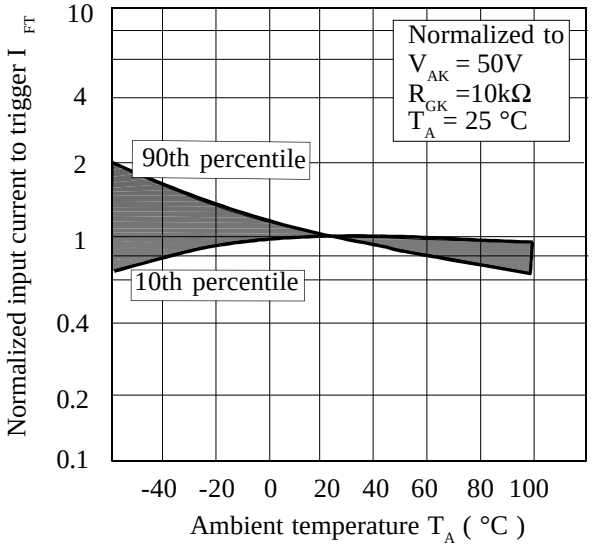
Input Current to Trigger vs. Anode to Cathode Voltage



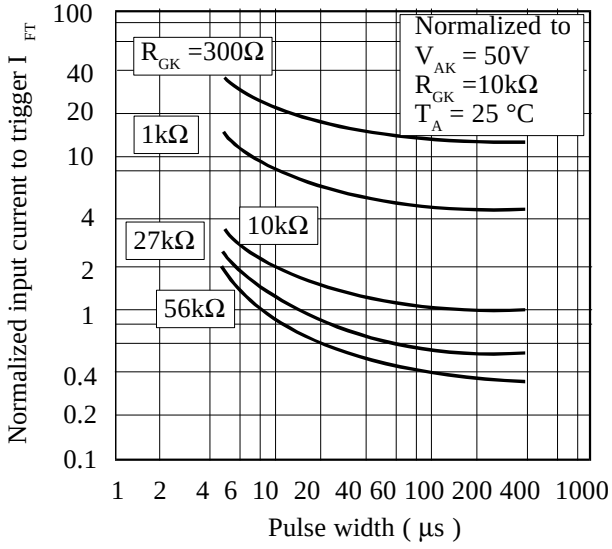
Input Current to Trigger vs. Ambient Temperature



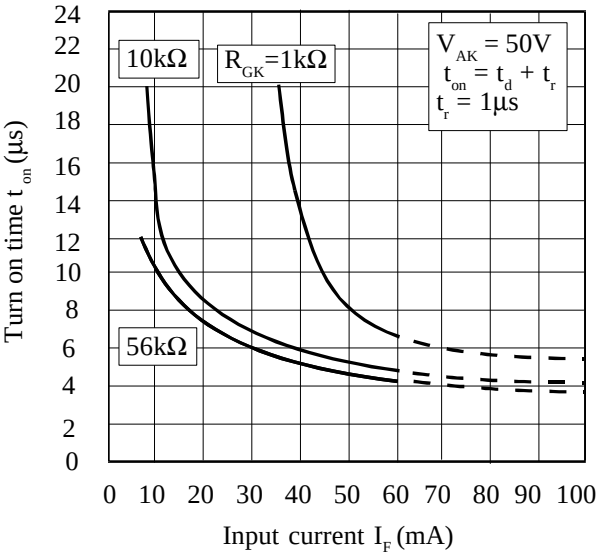
Input Current to Trigger Distribution vs. Ambient Temperature



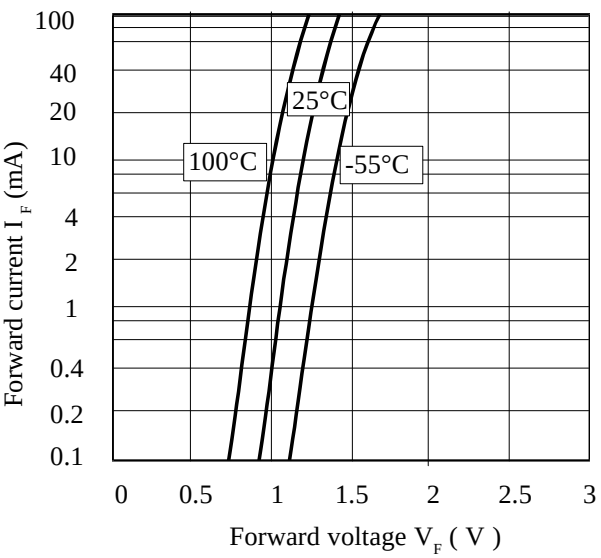
Input Current to Trigger vs. Pulse Width



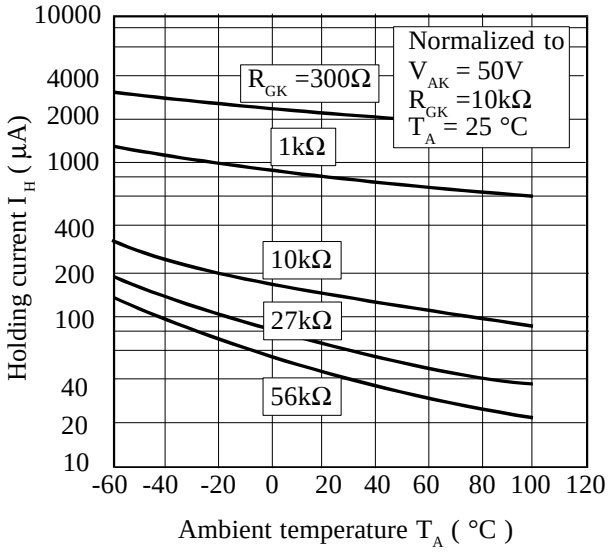
Turn on Time vs. Input Current



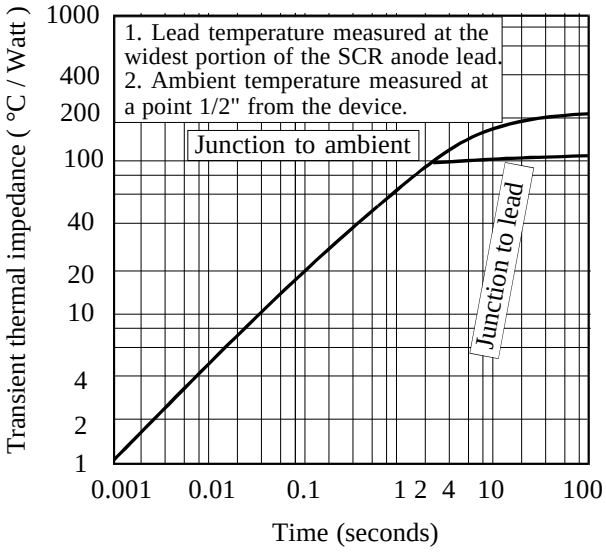
Input Characteristics I_F vs. V_F



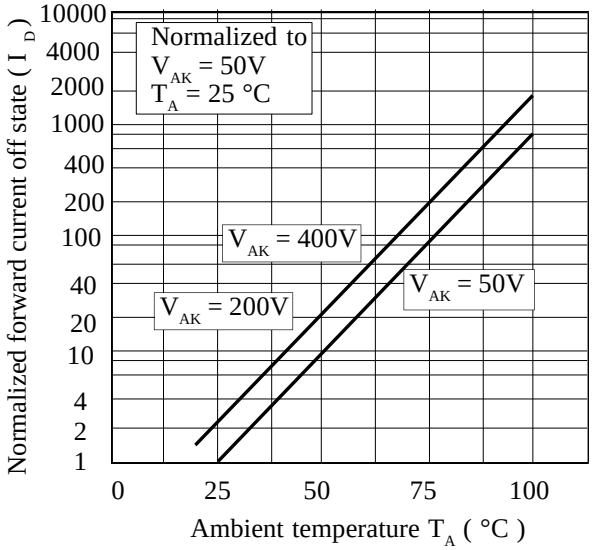
Holding Current vs. Ambient Temperature



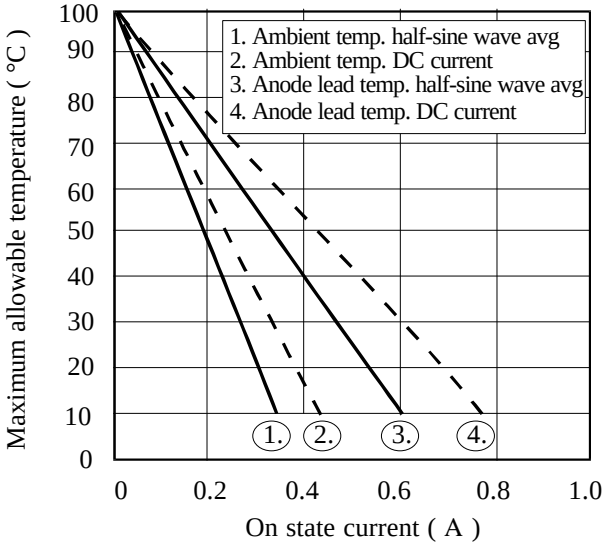
Maximum Transient Thermal Impedence


1. Lead temperature measured at the widest portion of the SCR anode lead.
2. Ambient temperature measured at a point 1/2" from the device.
Junction to ambient
Junction to lead
Transient thermal impedance (°C / Watt)
Time (seconds)

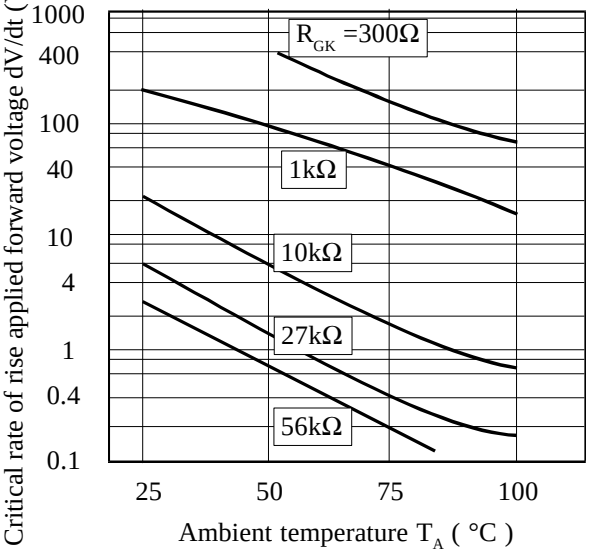
Off State Forward Current vs. Ambient Temperature



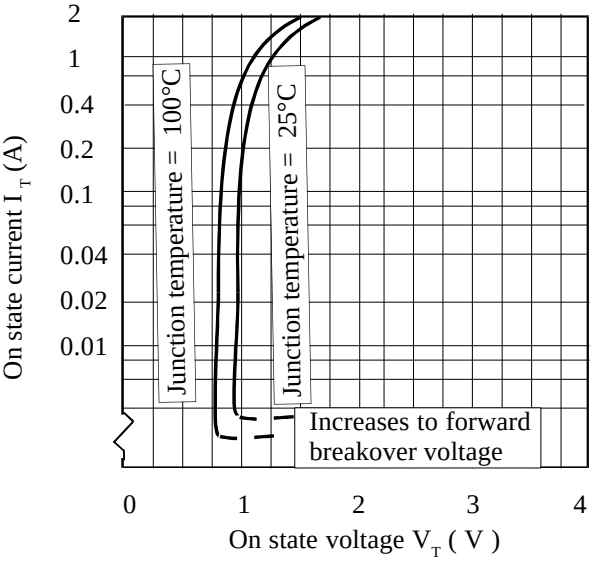
On State Current vs. Maximum Allowable Temperature


1. Ambient temp. half-sine wave avg
2. Ambient temp. DC current
3. Anode lead temp. half-sine wave avg
4. Anode lead temp. DC current
Maximum allowable temperature (°C)
On state current (A)

dV/dt vs. Ambient temperature



On State Characteristics


Junction temperature = 100°C
Junction temperature = 25°C
Increases to forward breakover voltage
On state current I_T (A)
On state voltage V_T (V)